

**MJ4032**  
**MJ4035**

**COMPLEMENTARY SILICON  
POWER DARLINGTON TRANSISTORS**

- COMPLEMENTARY PNP - NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

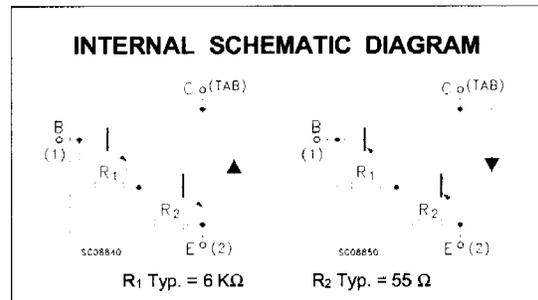
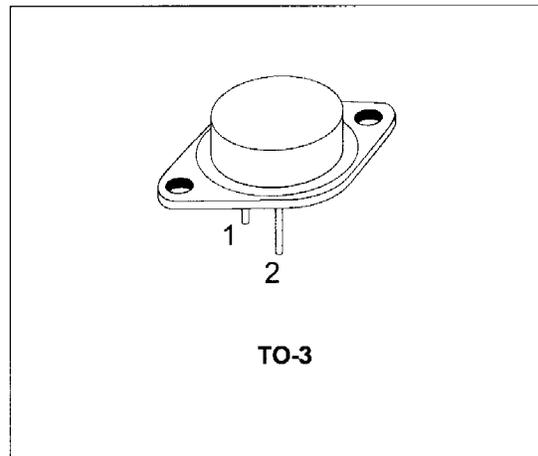
**APPLICATIONS**

- GENERAL PURPOSE SWITCHING
- GENERAL PURPOSE AMPLIFIERS

**DESCRIPTION**

The MJ4035 is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration mounted in Jedec TO-3 metal case. It is intended for use in general purpose and amplifier applications.

The complementary PNP type is the MJ4032.



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value		Unit
		PNP	MJ4032	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )		100	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )		100	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )		5	V
$I_C$	Collector Current		16	A
$I_B$	Base Current		0.5	A
$P_{tot}$	Total Dissipation at $T_c \leq 25^\circ C$		150	W
$T_{stg}$	Storage Temperature		-65 to 200	$^\circ C$
$T_j$	Max. Operating Junction Temperature		200	$^\circ C$

For PNP types voltage and current values are negative.

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**MJ4032 / MJ4035****THERMAL DATA**

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.17	°C/W
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**ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CER}$	Collector Cut-off Current ( $R_{BE} = 1\text{K}\Omega$ )	$V_{CE} = 100\text{ V}$ $V_{CE} = 100\text{ V}$ $T_c = 150\text{ }^{\circ}\text{C}$			1 5	mA mA
$I_{CEO}$	Collector Cut-off Current ( $I_B = 0$ )	$V_{CE} = 50\text{ V}$			3	mA
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5\text{ V}$			5	mA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage	$I_C = 100\text{ mA}$	100			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 10\text{ A}$ $I_B = 40\text{ mA}$ $I_C = 16\text{ A}$ $I_B = 80\text{ mA}$			2.5 4	V V
$V_{BE}^*$	Base-Emitter Voltage	$I_C = 10\text{ A}$ $V_{CE} = 3\text{ V}$			3	V
$h_{FE}^*$	DC Current Gain	$I_C = 10\text{ A}$ $V_{CE} = 3\text{ V}$	1000			

\* Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %  
For PNP type voltage and current values are negative.